

LTCC Technology for 60 GHz Applications

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ISMP 2006

LTCC Technology for 60 GHz Applications

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Outline

I Motivation

- Wireless Landscape
- 60 GHz Wireless Applications
- RoF based 60 GHz O/E Transceiver

II LTCC for 60 GHz

- Characteristics of substrate
- Characteristics of transmission line
- Characteristics of wire bonding
- Chip interconnection

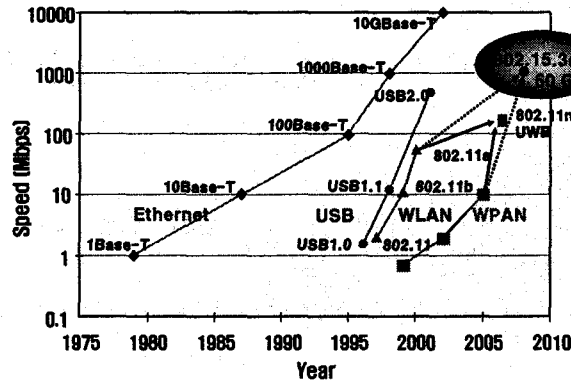
III Summary

Wireless Landscape



IEEE standards headed toward mm-wave WPAN (60 GHz)

- IEEE802.15.3c
 - Standard Working Group
 - Participation of over 20 Companies
- 60 GHz Band
 - World wide band allocations
 - 7 GHz bandwidth
 - 100 Mbps to multi-Gbps rates



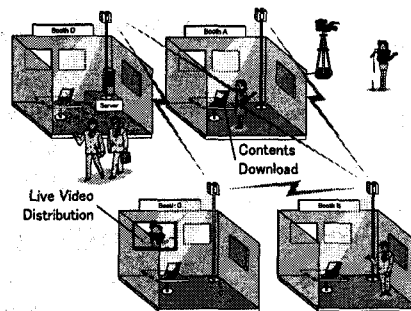
Drivers Include: Frequency allocation, bandwidth, capacity, power, cost, and reliability

60 GHz Wireless Applications

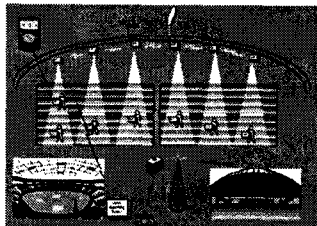


Ad-hoc Information distribution with Point-to-Point network extension :

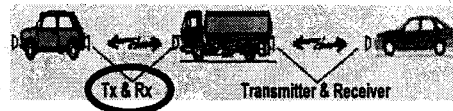
- Easy and immediate construction of temporal broadband network such as in exhibition-site for... Advertisement information distribution or Contents downloading service



Broadcasting video signal transmission system in sports stadium : ~1.5 Gbps



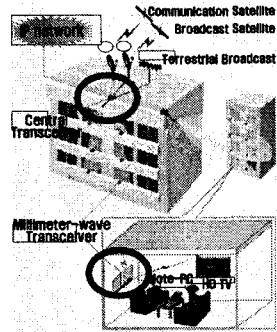
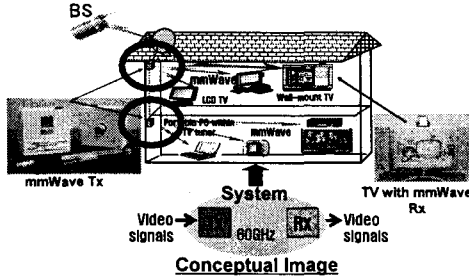
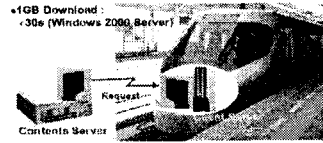
Inter-vehicle communication system



60 GHz Wireless Applications



- Huge data file transmission :
 - Ultra high speed download system
- mm-Wave video-signals transmission system :

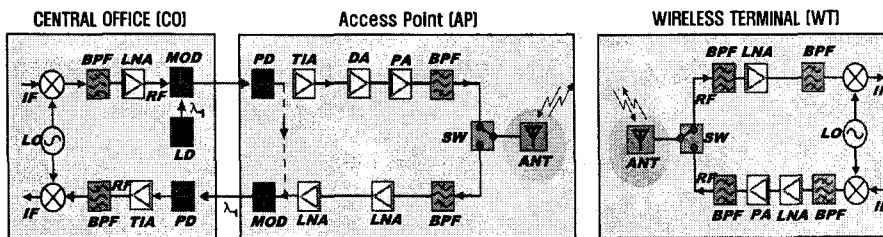


- Data Distribution at Apartments/condominiums :
 - mm-Wave PAN for on-demand transmission
 - re-broadcasting of video and data signal for ad-hoc terminals

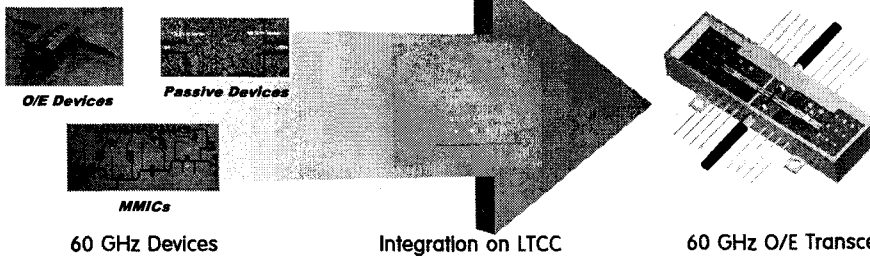
RoF based 60 GHz O/E Transceiver



- RoF (radio-over-fiber) based communication system



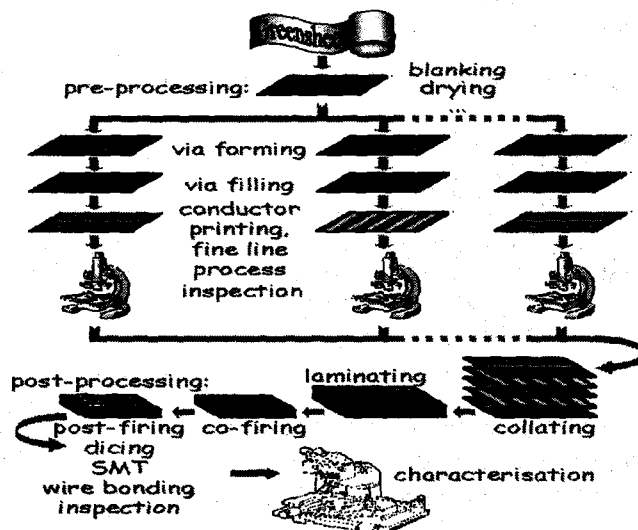
- 60 GHz O/E Transceiver SoP



LTCC for 60 GHz

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LTCC (low temperature co-fired ceramics) Technology



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LTCC for 60 GHz

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Is LTCC suitable for 60 GHz applications ?

Key Issues

- **Loss**
 - dielectric and conductor loss increase with frequency
- **Substrate solution**
 - Low dielectric loss at mmW-band, at 60 GHz
 - Low cost packaging materials
- **Transmission line solution**
 - low loss transmission at 60 GHz
- **Chip interconnection solution**
 - Low loss flip-chip or wire bond
 - Microstrip or CPW transmission line

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Characteristics of Substrate

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LTCC Greensheets for millimeter wave

Material Property	Units	A1	A2	B1	B2	
Electrical	- Dielectric Constant	(0.1~2 GHz)	7.8	7.4	5.9	5.9
	- Dielectric Loss Factor	(0.1~2 GHz)	0.0015	0.0005	0.0012	0.0012
Thermal	- Expansion Coefficient	(ppm/K)	5.8	6	7	> 8
	- Conductivity	(W/mK)	3.3	4.4	2	2
Mechanical	- Flexural Strength	(Mpa)	320	230	170	> 160
	- Young's Modulus	(Gpa)	120	150	92	92
Physical	- Green Tape Thickness	(mils)	4.5/6.5/10	2/5/10	5/10	5/10
	- Fired Tape Thickness	(mils)	3.6/5.4/8.1	1.8/4.5/9	3.7/7.4	3.9/7.8

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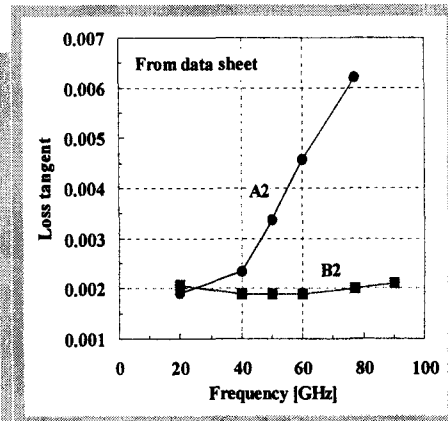
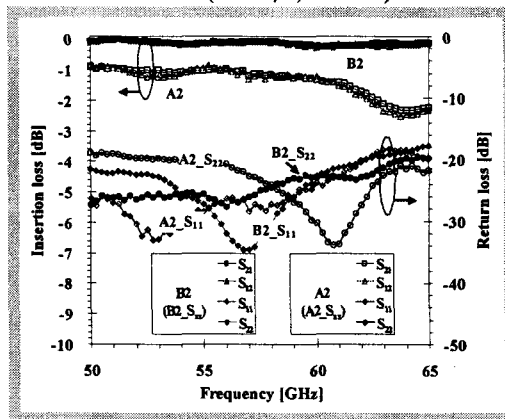
Characteristics of Substrate

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LTCC for millimeter-wave package

- Low insertion and return losses at 60 GHz and up to 90 GHz
- Low material cost & multi-layer possible

CPW ($h=100\mu\text{m}$, $L=4\text{mm}$)



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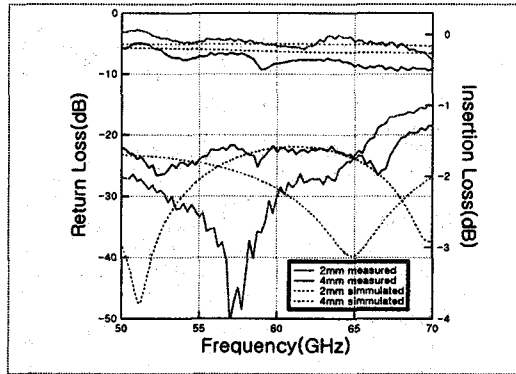
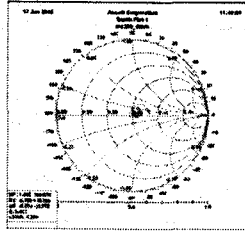
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Characteristics of transmission Line



Microstrip line (1 layer)

Dielectric Thickness: 100 μm



Thickness	Line length	S11[dB]	S21[dB]	S12[dB]	S22[dB]
1 layer (100 μm)	2mm	-31.1	-0.16	-0.18	-29.7
	4mm	-22.8	-0.41	-0.42	-24.3

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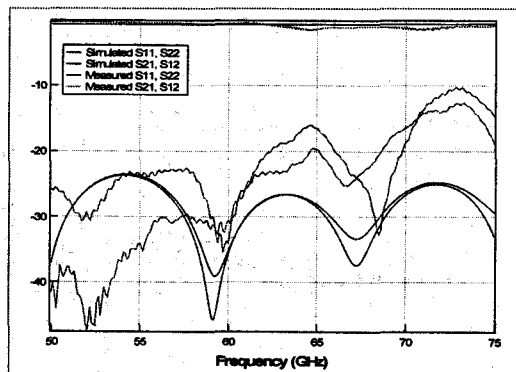
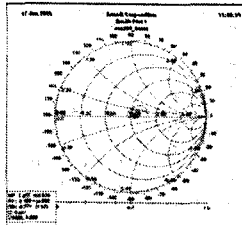
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Characteristics of transmission Line



Microstrip line (2 layers)

Dielectric Thickness: 200 μm



Thickness	Line length	S11[dB]	S21[dB]	S12[dB]	S22[dB]
2 layers (200 μm)	4mm	-23.9	-1.25	-1.18	-17.3
	6mm	-30.6	-0.58	-0.52	-34.0

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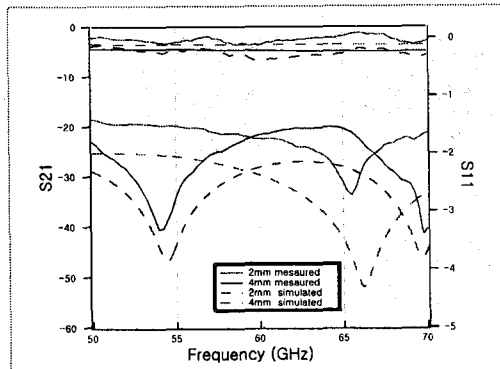
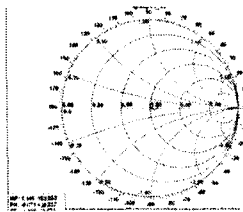
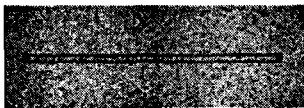
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Characteristics of transmission Line



■ CBCPW line (1 layer)

- Dielectric Thickness: 100 μm



Thickness	Line length	S11[dB]	S21[dB]	S12[dB]	S22[dB]
1 layer (100 μm)	2mm	-22.4	-0.15	-0.12	-20.4
	4mm	-21.7	-0.40	-0.37	-22.4

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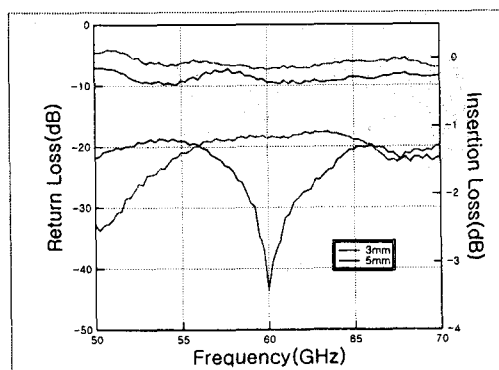
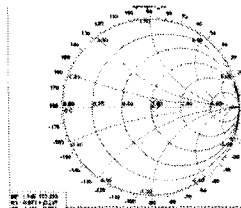
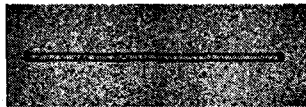
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Characteristics of transmission Line



■ CBCPW line (2 layers)

- Dielectric Thickness: 200 μm



Thickness	Line length	S11[dB]	S21[dB]	S12[dB]	S22[dB]
2 layers (200 μm)	3mm	-18.6	-0.16	-0.17	-19.1
	5mm	-43.5	-0.35	-0.39	-27.3

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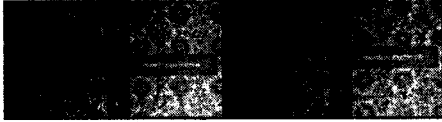
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Characteristics of Interconnection

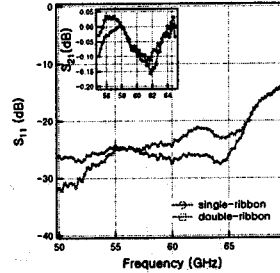
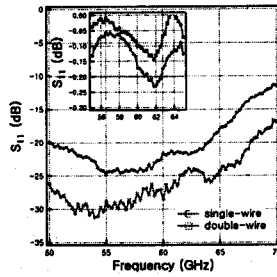
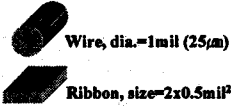
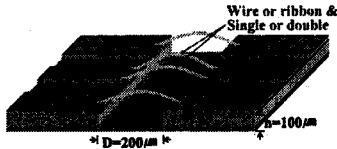


Wire bonding

● CBCPW Line (Dielectric thickness: 100 μm)



Type of bonding	S11	S12
single wire	- 21.6dB	- 0.17dB
double wire	- 28.6dB	- 0.10dB
single ribbon	- 27.4dB	- 0.10dB
double ribbon	- 24.3dB	- 0.09dB



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Characteristics of Interconnection

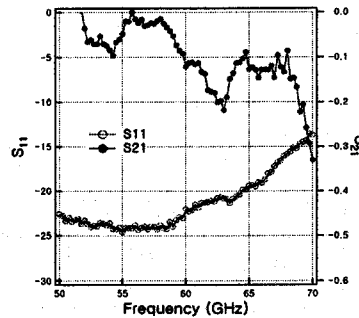
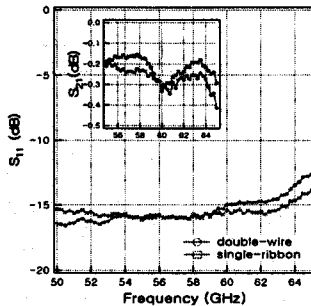


Wire bonding

● CBCPW Line (Dielectric thickness: 200 μm)



Type of bonding	S11	S12
single wire	- 9.19dB	- 0.75dB
double wire	- 14.5dB	- 0.35dB
single ribbon	- 15.4dB	- 0.31dB
double ribbon	- 22.1dB	- 0.12dB



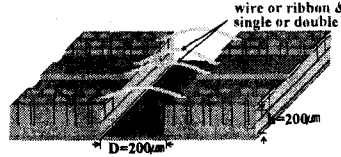
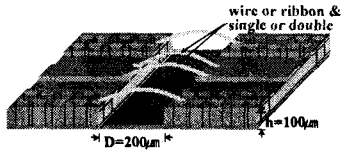
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Characteristics of Interconnection



■ Influence of dielectric thickness



Dielectric thickness (100µm)

- Single ribbon or double wire bonding
 - nearly 50 Ohm at 60 GHz
- Low loss transmission
- S_{21} : -0.1dB, S_{11} : -20dB

Dielectric thickness (200µm)

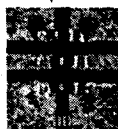
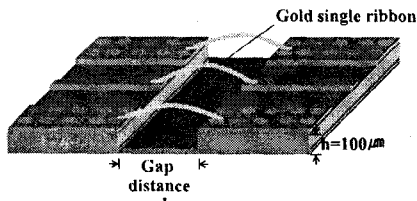
- Single ribbon or double wire bonding
 - high Impedance state
- To match 50Ω, increase the line width.
- Double ribbon bonding is required.
- Low loss transmission
- S_{21} : -0.1dB, S_{11} : -20dB

Characteristics of Interconnection

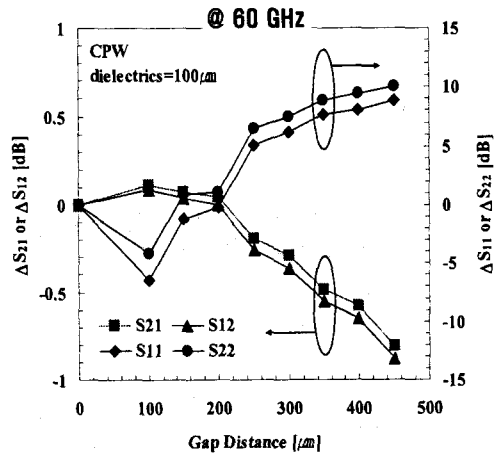


■ Interconnection loss from wire length

- Gap distance : acceptable RF degradation during the interconnection



Photograph of 100µm gap

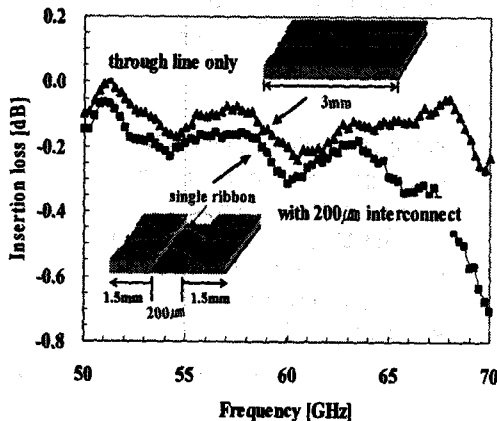


Characteristics of Interconnection



Interconnect loss of wire-bonding

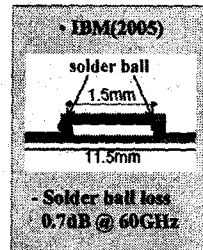
- low loss and simple process : Wire-Bonding technique
- symmetric performance ($S_{11} \approx S_{22}$) of wedge bonding method



Wire-bonding



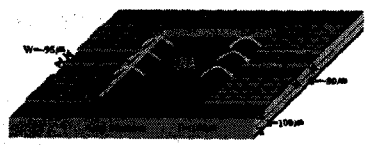
Flip-chip bonding



Chip Interconnection



Considerations for MMIC module

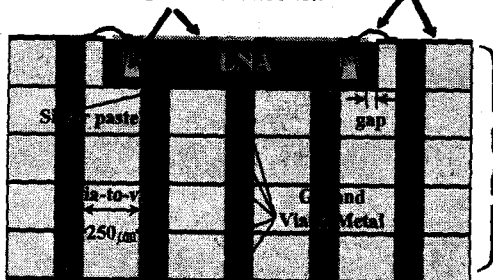


Solutions for Mounting

- cavity structure
- via-hole ground connection

Solutions for Interconnection

- CPW line
- ribbon wedge bonding



Solutions for Materials

- low loss substrate
- internal silver conductor
- external gold conductor

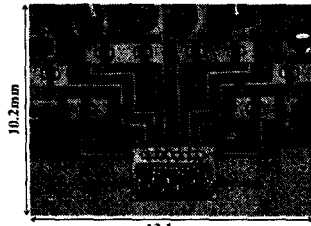
Chip Interconnection



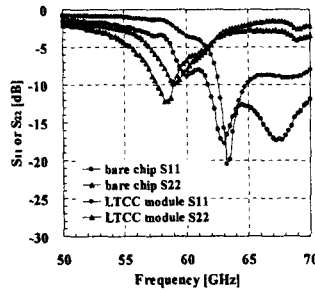
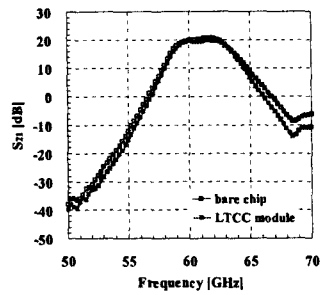
■ LNA (low noise amplifier) Module

● S-parameter measurement

- by hp8720C N/A
- frequency: 50~70 GHz
- S_{21} = -19.4dB and $\angle S_{21}$ = -0.4 dB
- S_{11} = -3.5dB and $\angle S_{11}$ = -5.3 dB
- S_{22} = -7.9dB and $\angle S_{22}$ = 1.2 dB



LNA Module



Summary



LTCC Technology is very suitable for 60 GHz application

- LTCC substrate shows low loss at 60 GHz.
 - low insertion and return losses
- Microstrip or CBCPW line is suitable for transmission lines at 60 GHz.
 - low loss (0.1dB/mm)
- Single ribbon bonding is adequate for interconnection
 - simple
 - low loss (0.1dB/bonding)
- Characteristics of MMIC module
 - Gain difference ($\angle S_{21}$): 0.4 dB